

Epitaxial Planar NPN Transistor

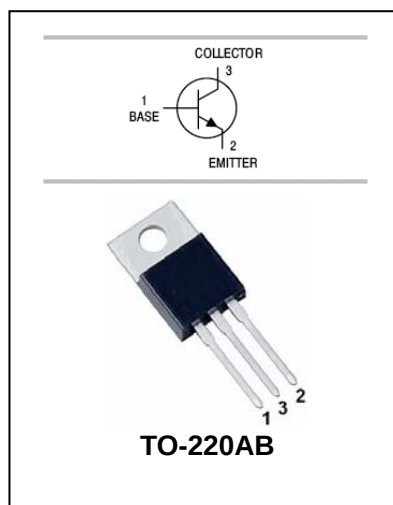
2SC4544

FEATURES

- High Voltage.
- Small Collector Output Capacitance.
- Collector Metal is Fully Covered With Mold Resin.



Lead-free



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current	100	mA
I_B	Base Current	50	mA
P_C	Collector Dissipation $T_a=25^{\circ}\text{C}$ $T_c=25^{\circ}\text{C}$	2 8	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	$^{\circ}\text{C}$

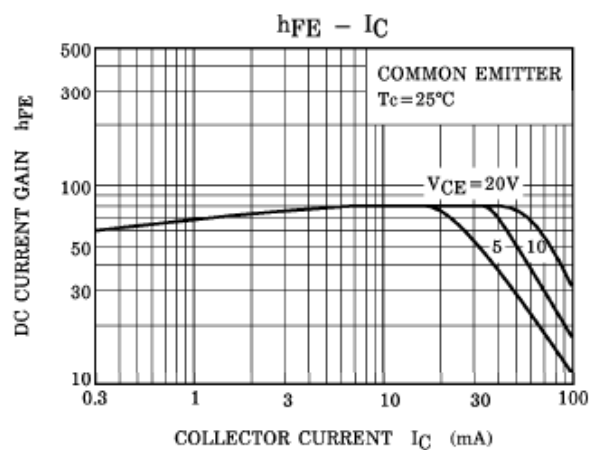
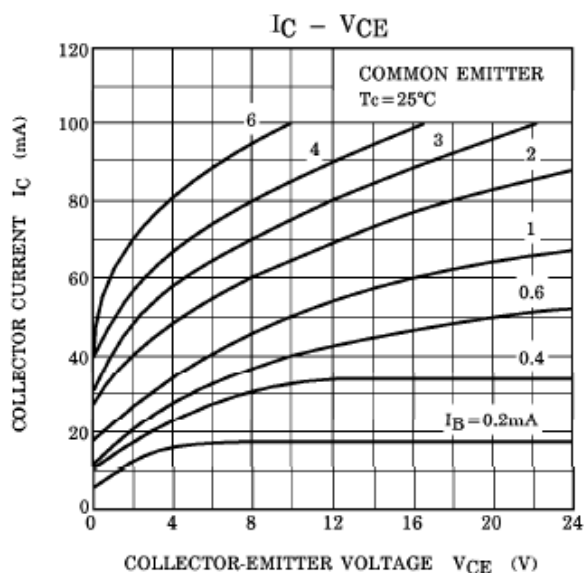
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ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

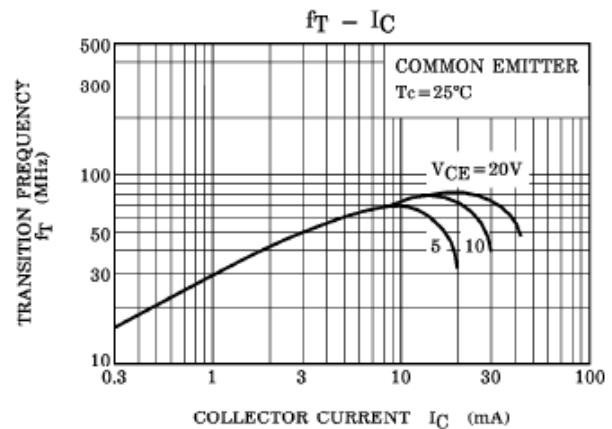
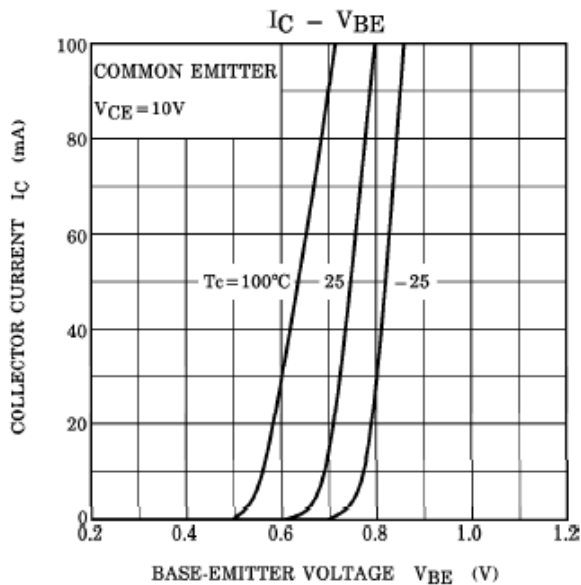
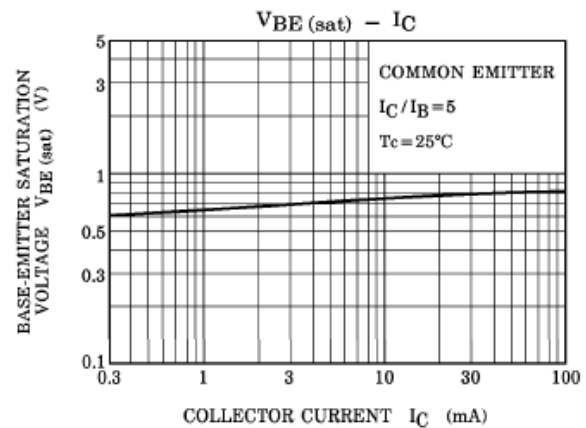
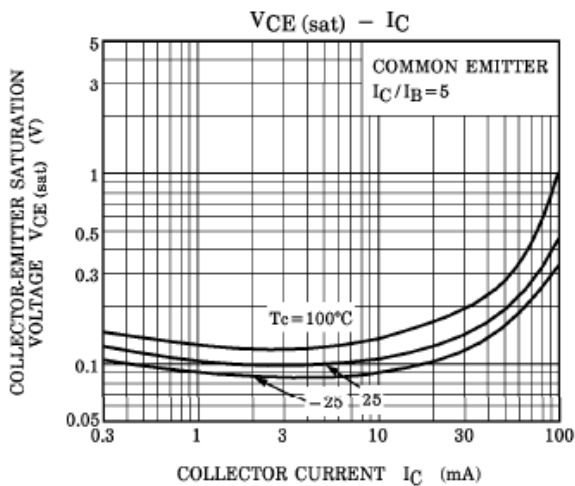
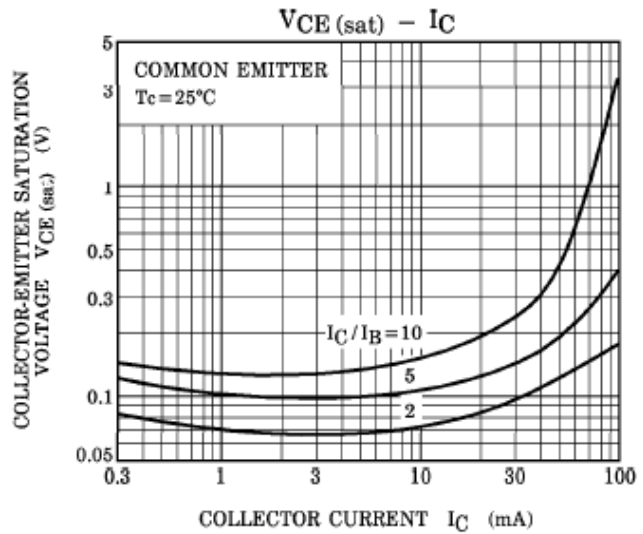
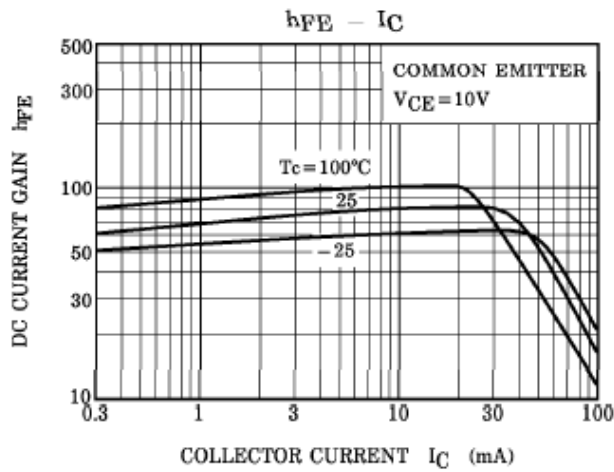
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=240V, I_E=0$			1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$			1	μA
DC Current Gain	h_{FE}	$V_{CE}=10V, I_C=4mA$ $V_{CE}=10V, I_C=20mA$	20 30		200	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Transition Frequency	f_T	$V_{CE}=10V, I_C=20mA$	50	70		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=20V, I_E=0,$ $f=1MHz$		3		pF

TYPICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified



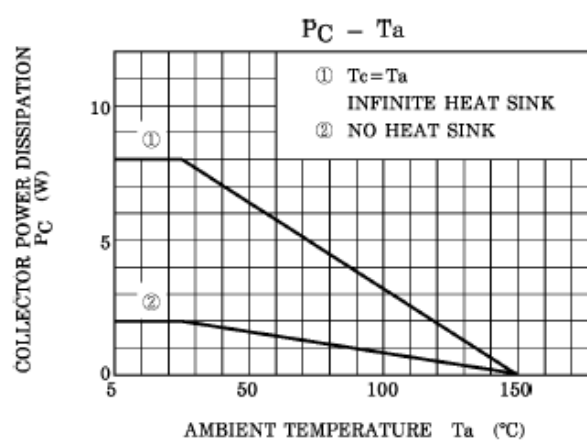
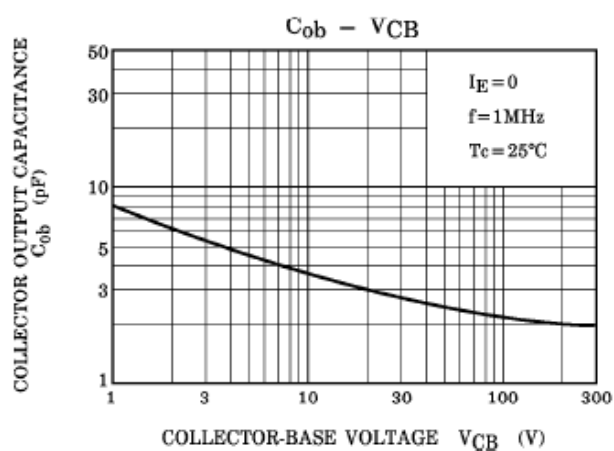
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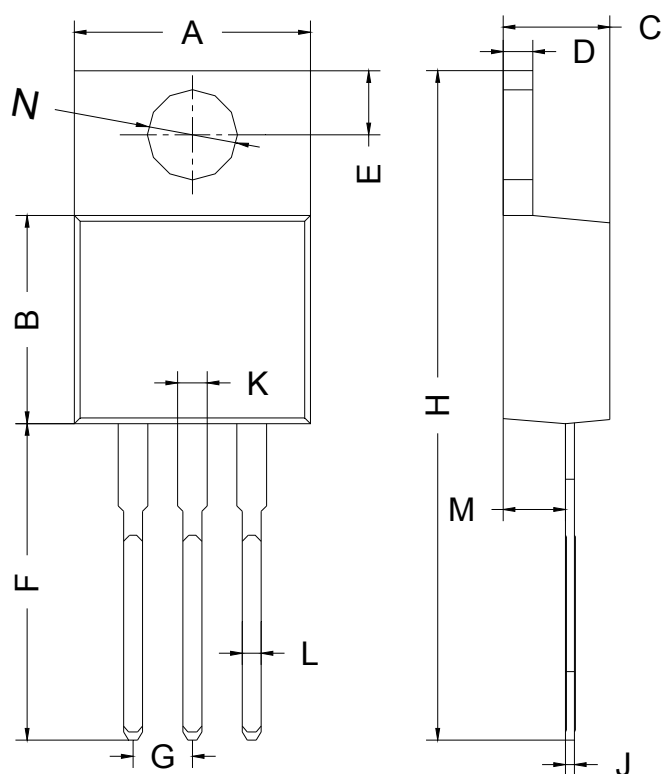
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PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB



TO-220AB		
Dim	Min	Max
A	9.80	10.30
B	8.70	9.10
C	4.57 Typical	
D	1.27 Typical	
E	2.64	2.84
F	13.34	13.74
G	2.44	2.64
H	28.43	28.83
J	0.38 Typical	
K	1.22	1.32
L	0.71	0.91
M	2.50 Typical	
N	3.86 Typical	
All Dimensions in mm		